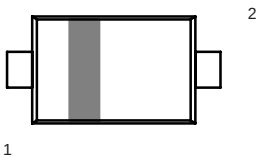
MSV SEMI

1N5819

FEATURES

- **Low Forward Voltage Drop**
- **Guard Ring Construction for Transient Protection**
- **Negligible Reverse Recovery Time**
- **Low Reverse Capacitance**

SOD-123



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25℃

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage **Working Peak** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	I_{FM}	350	mA
Repetitive Peak Forward Current @t≤1.0s	I_{FRM}	1.5	A
Power Dissipation	Pd	400	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	300	℃/W
Storage temperature	T_{STG}	-65~+125	℃

Electrical Ratings @T_A=25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	40			V	I_R=100μA
Forward voltage	V_F			0.37 0.60	V	I_F=20mA I_F=200mA
Reverse current	I_{RM}			5.0	μA	V_R=30V
Capacitance between terminals	C_T			50	pF	V_R=0V,f=1.0MHz
Reverse Recovery Time	t_{rr}		10		ns	I_F=I_R=200mA Irr=0.1XI_R,R_L=100Ω

Typical Characteristics

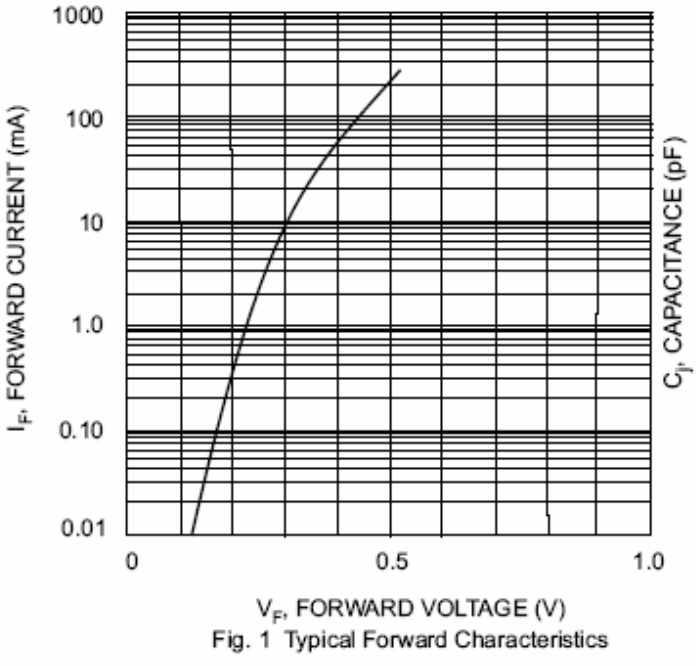


Fig. 1 Typical Forward Characteristics

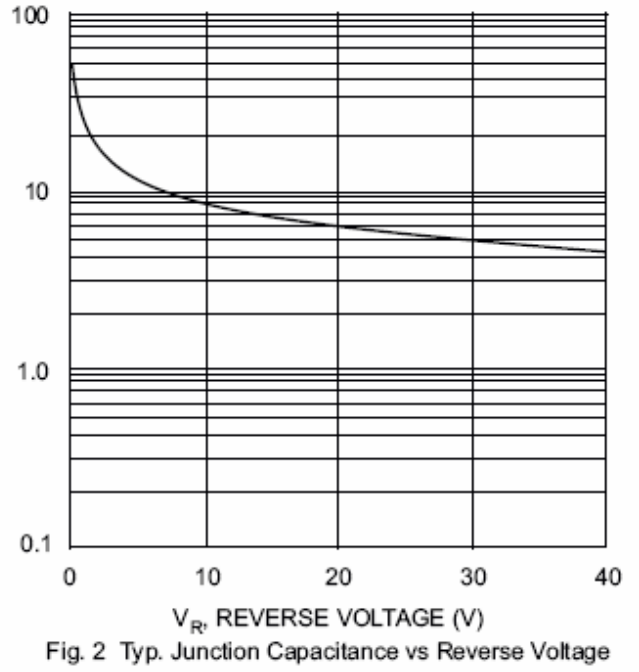


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage